Supporting Information

Small-Signal Modeling and Nonlinear Characterization of Aligned Carbon Nanotube Schottky Barrier Diodes

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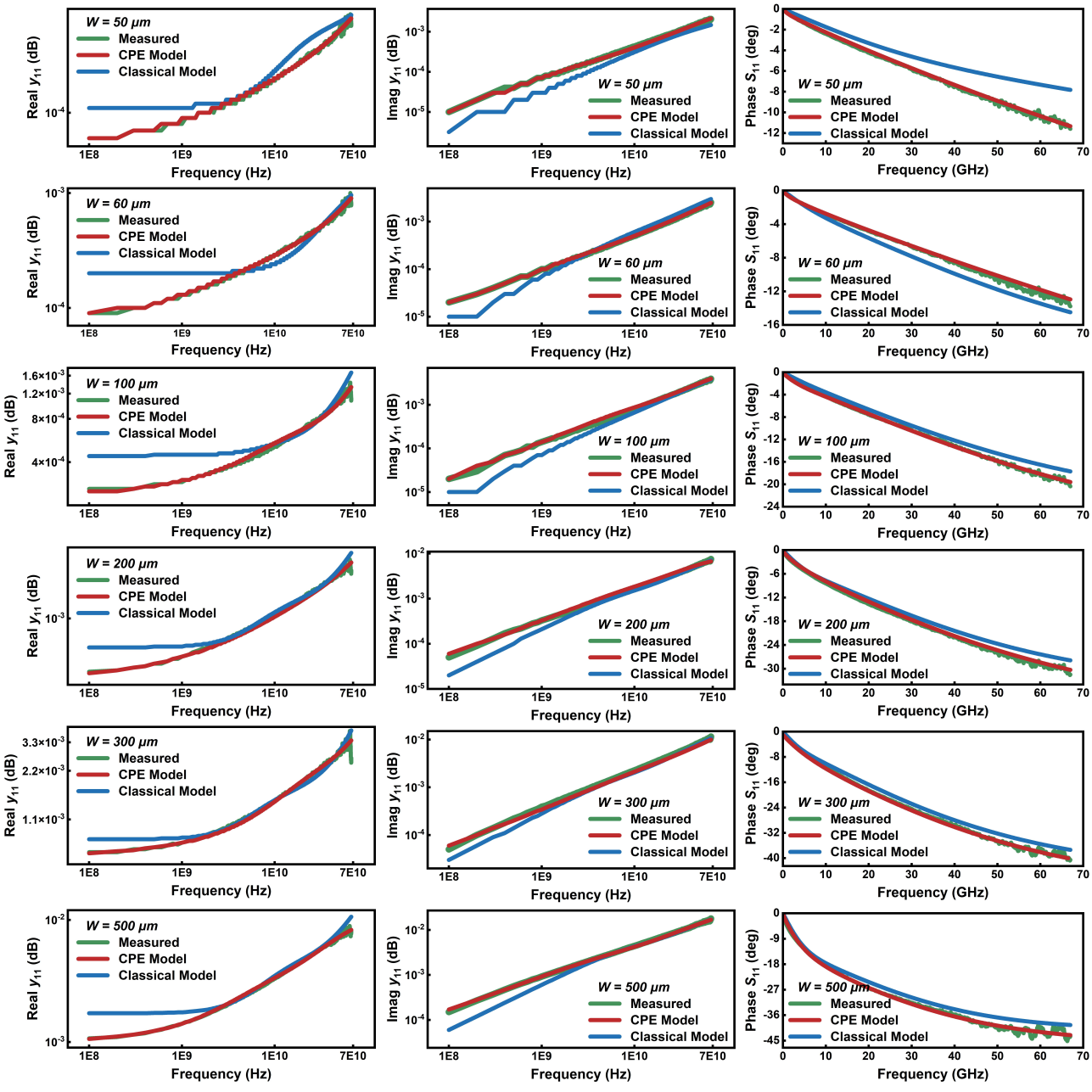


Figure S1. Comparison of S-parameters obtained from measurement, classical model, and CPE-based model for ACNT-SBDs with different channel widths under 0.4 V bias.